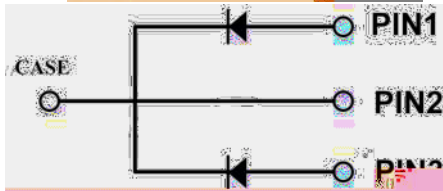
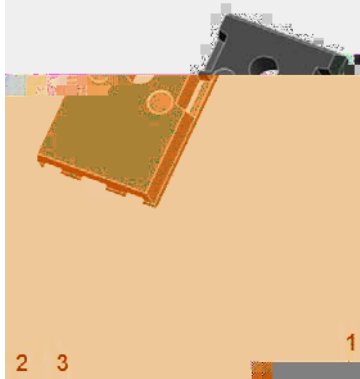


Silicon Carbide Schottky Diode

V_{RRM}	650V
I_F 135°C	52A ⁽²⁾
Q_C	124nC ⁽²⁾



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

Package: TO-247AB

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free

Terminals: Tin plated leads

Polarity: As marked

Maximum Ratings ($T_c=25$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D106540NCTQG2
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	V_{RRM}	V	650
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	V_{RSM}	V	650
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	V_{DC}	V	650
Continuous forward current @ $T_c=25^\circ\text{C}$	I_F	A	56/112
Continuous forward current @ $T_c=135^\circ\text{C}$			26/52
Continuous forward current @ $T_c=148^\circ\text{C}$			20/40
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	I_{FSM}	A	160 ⁽¹⁾
Power Dissipation @ $T_c=25^\circ\text{C}$	P_{TOT}	W	187/365
Power Dissipation @ $T_c=110^\circ\text{C}$			81/158
i^2t Value @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	i^2t	A ² S	128 ⁽¹⁾
Operating junction and Storage temperature range	T_j, T_{stg}	°C	-55 to +175

(1) Per Leg, (2) Per Device



Electrical Characteristics (Per Leg)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	V_F	V	$I_F=20A, T_J=25^{\circ}C$	1.35	1.55
			$I_F=20A, T_J=175^{\circ}C$	1.75	-

V_R

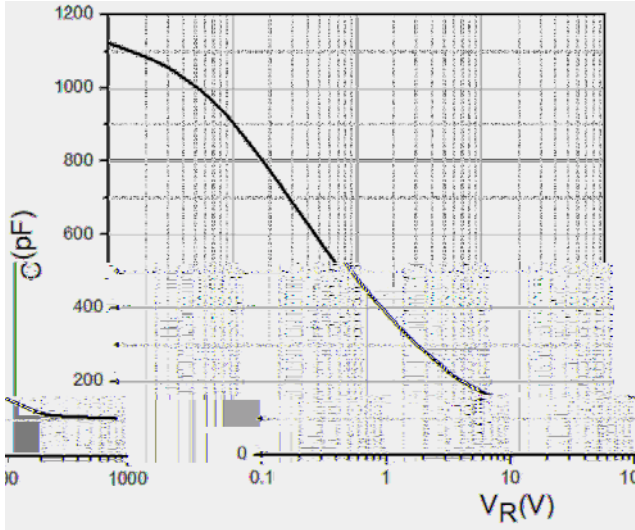


Figure 3. Capacitance vs. Reverse Voltage

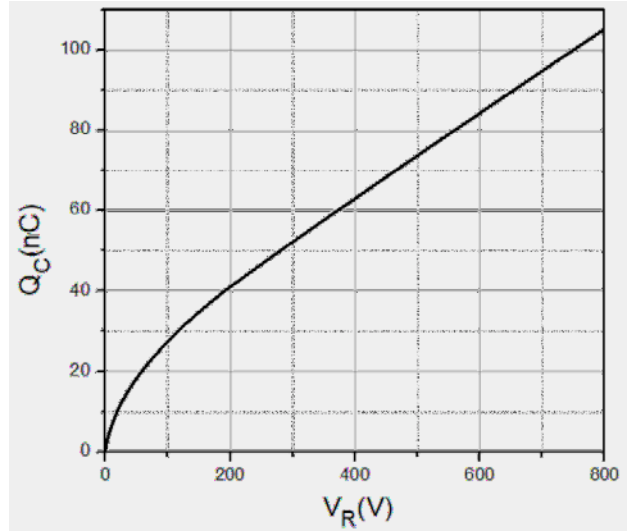


Figure 4. Total Capacitance Charge vs. Reverse Voltage

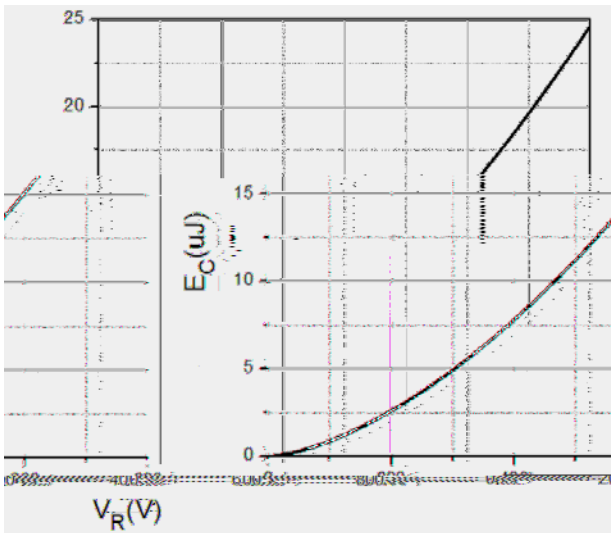


Figure 5. Capacitance Stored Energy

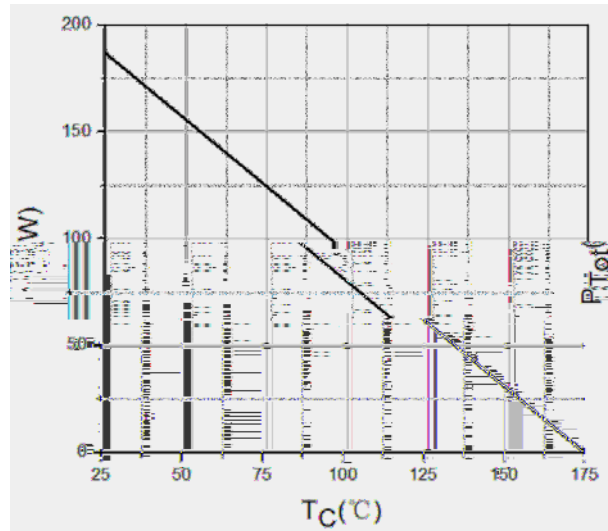


Figure 6. Power Derating

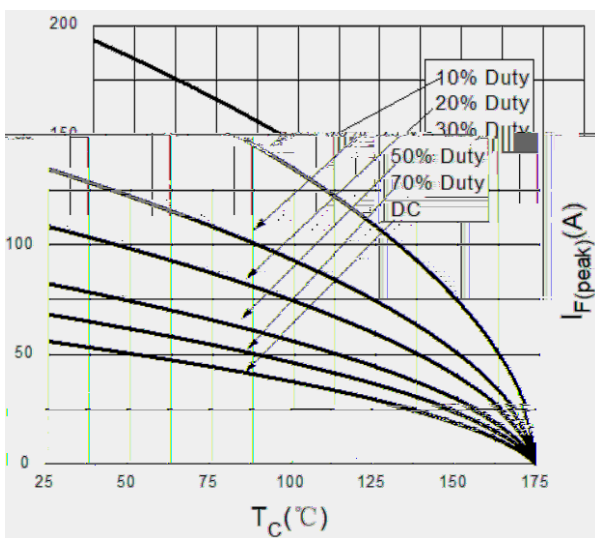


Figure 7. Current Derating

Typical Characteristics (Device)

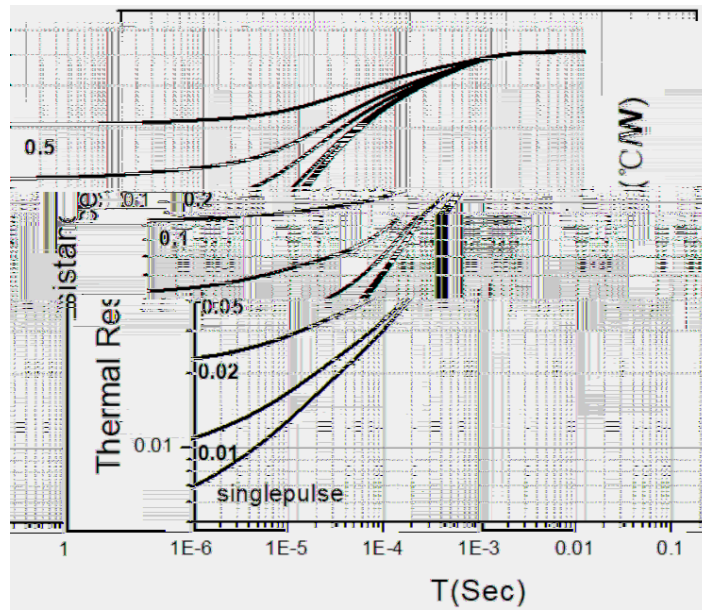
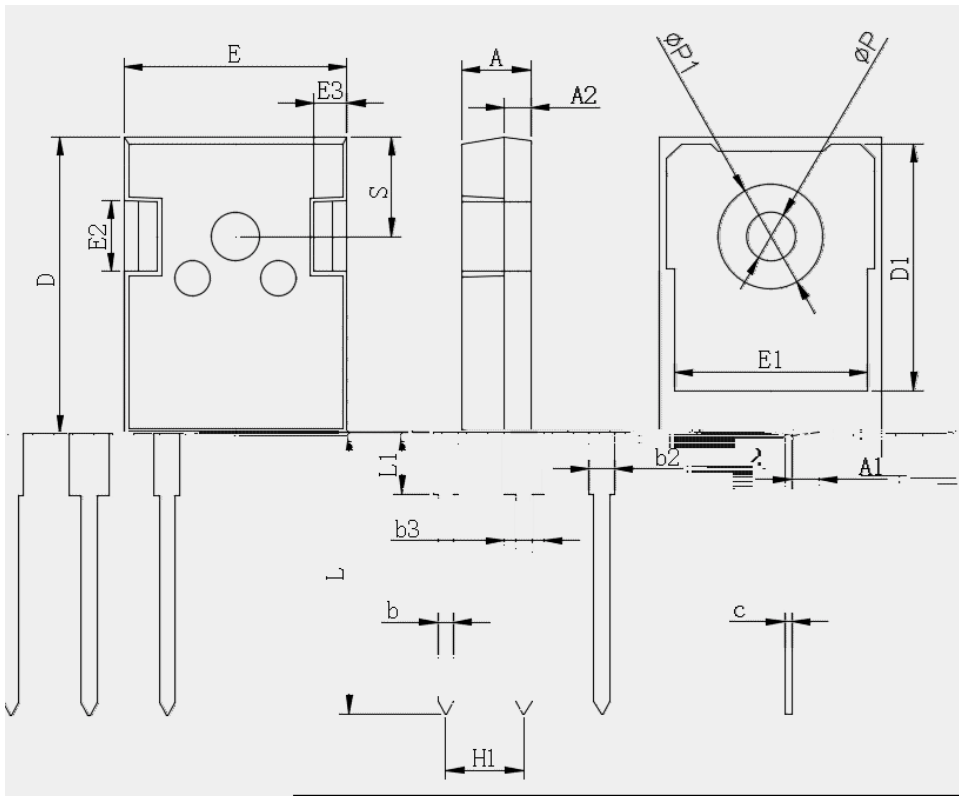


Figure 8. Transient Thermal Impedance



Outline Dimensions



TO-247AB		
Dim	Min	Max
A	4.8	5.2
A1	2.21	2.61
A2	1.85	2.15
b	1	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.7	21.3
D1	16.25	16.85
E	15.5	16.1
E1	1.4	1.8
E2	4.8	5.2
E3	2.3	2.7
L	19.62	20.2
L1	-	4.3
ΦP	3.4	3.8
ΦP1		7.3
S		6.15TYP
H1		5.44TYP

